

**UTC** UNISONIC TECHNOLOGIES CO., LTD

## **BD237**

NPN EPITAXIAL SILICON TRANSISTOR

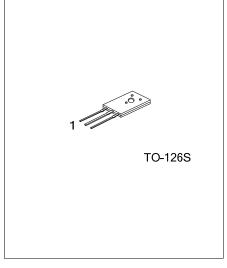
## **80V, NPN TRANSISTORS**

#### DESCRIPTION

The UTC BD237 is an NPN transistor. it uses UTC's advanced technology to provide customers with high collector-emitter breakdown voltage, etc.

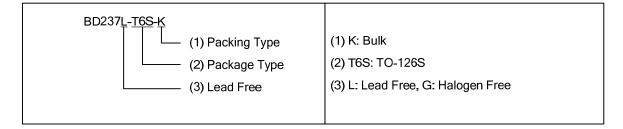
#### **FEATURES**

- \* Complement to UTC BD238 respectively
- \* High collector-emitter breakdown voltage



#### ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BD237L-T6S-K	BD237G-T6S-K	TO-126S	E	С	В	Bulk	





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### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Continuous Collector Current	lc	2	А
Collector Dissipation	Pc	1.25	W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>STG</sub>	-65~150	°C

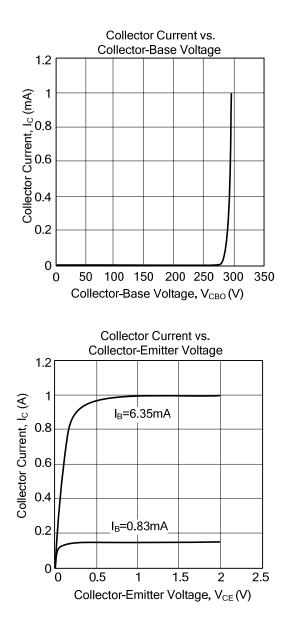
Note: Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

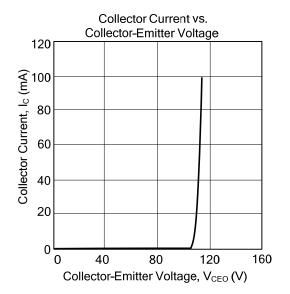
### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub> =25°C, unless otherwise specified)

PARAMETER	ARAMETER SYMBOL TEST CONDITIONS		MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	100			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =0	80			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	$I_E=1mA$ , $I_C=0$	5			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =100V, I <sub>E</sub> =0			100	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	$V_{EB}=5V, I_{C}=0$			1	mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =100mA			0.6	V
DC Current Coin	h <sub>FE</sub> (1)	I <sub>C</sub> =150mA,V <sub>CE</sub> =2V	40			
DC Current Gain	h <sub>FE</sub> (2)	I <sub>C</sub> =1A,V <sub>CE</sub> =2V	25			
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> =250mA, V <sub>CE</sub> =10V, f=10MHz	3			MHz

## NPN EPITAXIAL SILICON TRANSISTOR

### TYPICAL CHARACTERISTICS





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